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Single 2-Input NAND Gate

MC74HC1G00

The MC74HC1G00 is a high speed CMOS 2-input NAND gate fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The MC74HC1G00 output drive current is 1/2 compared to MC74HC series.

Features

- High Speed: $t_{PD} = 7 \text{ ns} (Typ)$ at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1 \ \mu A (Max)$ at $T_A = 25^{\circ}C$
- High Noise Immunity
- Balanced Propagation Delays (t_{pLH} = t_{pHL})
- Symmetrical Output Impedance $(I_{OH} = I_{OL} = 2 \text{ mA})$
- Chip Complexity: < 100 FETs
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

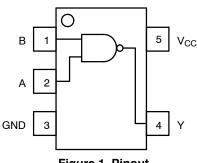
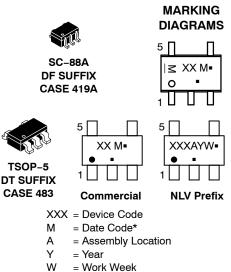






Figure 2. Logic Symbol

PIN ASSIGNMENT						
1	В					
2	А					
3	GND					
4	Y					
5	V _{CC}					



= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

5 1 SC-74A DBV SUFFIX CASE 318BQ

XXX = Specific Device Code M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inp	uts	Output
А	в	Y
L	L	Н
L	н	Н
н	L	Н
Н	Н	L

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 6 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		–0.5 to +6.5	V
V _{IN}	DC Input Voltage		–0.5 to V _{CC} +0.5	V
V _{OUT}	DC Output Voltage		–0.5 to V _{CC} +0.5	V
I _{IK}	DC Input Diode Current		±20	mA
Ι _{ΟΚ}	DC Output Diode Current		±20	mA
I _{OUT}	DC Output Source/Sink Current		±12.5	mA
$I_{CC} \text{ or } I_{GND}$	DC Supply Current per Supply Pin or Ground Pin		±25	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)	SC-88A SC-74A	377 320	°C/W
P _D	Power Dissipation in Still Air at 85°C	SC–88A SC–74A	332 390	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	2000 1000	V
ILATCHUP	Latchup Performance (Note 3)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 20 ounce copper trace with no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued per JEDEC/JEP172A.

3. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	6.0	V
V _{IN}	DC Input Voltage	0.0	V _{CC}	V
V _{OUT}	DC Output Voltage	0.0	V _{CC}	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 6.0 \text{ V}$	0 0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

			V _{CC}	Т	A = 25°	С	-40°C ≤ 1	Γ _A ≤ 85°C	–55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.20	- - -	- - -	1.5 2.1 3.15 4.20	- - - -	1.5 2.1 3.15 4.20	- - - -	V
V _{IL}	Low-Level Input Voltage		2.0 3.0 4.5 6.0	- - -	- - -	0.5 0.9 1.35 1.80	- - -	0.5 0.9 1.35 1.80	- - - -	0.5 0.9 1.35 1.80	V
V _{OH}	High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -20 \ \mu A$	2.0 3.0 4.5 6.0	1.9 2.9 4.4 5.9	2.0 3.0 4.5 6.0	- - -	1.9 2.9 4.4 5.9	- - - -	1.9 2.9 4.4 5.9	- - - -	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -2 \text{ mA}$ $I_{OH} = -2.6 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80		4.13 5.63		4.08 5.58		
V _{OL}	Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 20 \ \mu A$	2.0 3.0 4.5 6.0	- - -	0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1	- - -	0.1 0.1 0.1 0.1	- - - -	0.1 0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 2 \text{ mA}$ $I_{OL} = 2.6 \text{ mA}$	4.5 6.0		0.17 0.18	0.26 0.26	- -	0.33 0.33		0.40 0.40	
I _{IN}	Input Leakage Current	V _{IN} = 6.0 V or GND	6.0	-	-	±0.1	-	±1.0	-	±1.0	μΑ
Icc	Quiescent Supply Current	V _{IN} = V _{CC} or GND	6.0	_	_	1.0	-	10	-	40	μΑ

DC ELECTRICAL CHARACTERISTICS

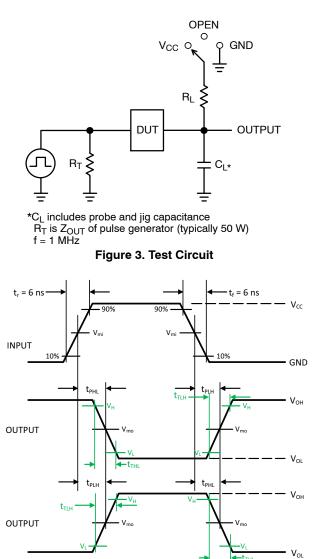
MC74HC1G00

AC ELECTRICAL CHARACTERISTICS

			Т	$T_{A} = 25^{\circ}C \qquad -40^{\circ}C \leq T_{A} \leq 85$		Γ _A ≤ 85°C	-55°C ≤ T	A ≤ 125°C		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay,	$V_{CC} = 5.0 \text{ V}$ $C_{L} = 15 \text{ pF}$	-	3.5	15	-	20	-	25	ns
tphl	(A or B) to Y	$\begin{array}{ll} V_{CC} = 2.0 \ V & C_L = 50 \ pF \\ V_{CC} = 3.0 \ V \\ V_{CC} = 4.5 \ V \\ V_{CC} = 6.0 \ V \end{array}$	- - -	20 11 8 7	100 27 20 17	- - -	125 35 25 21	- - - -	155 90 35 26	
t _{TLH} ,	Output Transition	$V_{CC} = 5.0 \text{ V}$ $C_{L} = 15 \text{ pF}$	-	3	10	-	15	-	20	ns
t _{THL}	Time	$\begin{array}{ll} V_{CC} = 2.0 \ V & C_L = 50 \ pF \\ V_{CC} = 3.0 \ V & \\ V_{CC} = 4.5 \ V & \\ V_{CC} = 6.0 \ V & \end{array}$	- - -	25 16 11 9	125 35 25 21	- - - -	155 45 31 26	- - - -	200 60 38 32	
C _{IN}	Input Capacitance		-	5	10	-	10	-	10	pF
						Typical @	25°C, V _{CC}	= 5.0 V		
C _{PD}	Power Dissipation Ca	apacitance (Note 4)					10			pF

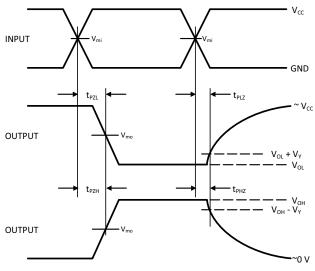
4. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

MC74HC1G00



Test	Switch Position	C _L , pF	R_L, Ω
t_{PLH} / t_{PHL}	Open		Х
t _{TLH} / t _{THL} (Note 5)	Open	See AC Characteristics Table	х
t _{PLZ} / t _{PZL}	V _{CC}	Table	1 k
t_{PHZ} / t_{PZH}	GND		1 k

X - Don't Care





		V _{mo} , V				
v_{cc}, v	V _{mi} , V	t _{PLH} , t _{PHL}	$t_{\text{PZL}}, t_{\text{PLZ}}, t_{\text{PZH}}, t_{\text{PHZ}}$	V _L , V	V _H , V	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{OL} + 0.1 (V _{OH} – V _{OL})	V _{OL} + 0.9 (V _{OH} – V _{OL})	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{OL} + 0.1 (V _{OH} – V _{OL})	V _{OL} + 0.9 (V _{OH} – V _{OL})	0.3

5. t_{TLH} and t_{THL} are measured from 10% to 90% of (V_{OH} - V_{OL}), and 90% to 10% of (V_{OH} - V_{OL}), respectively.

MC74HC1G00

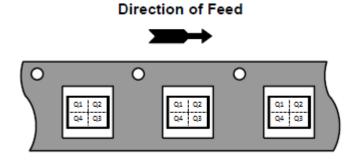
ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
MC74HC1G00DFT1G	SC-88A	H1	Q2	3000 / Tape & Reel
MC74HC1G00DFT1G-Q*	SC-88A	H1	Q2	3000 / Tape & Reel
MC74HC1G00DFT2G	SC-88A	H1	Q4	3000 / Tape & Reel
MC74HC1G00DFT2G-Q*	SC-88A	H1	Q4	3000 / Tape & Reel
MC74HC1G00DBVT1G	SC-74A	H1	Q4	3000 / Tape & Reel
MC74HC1G00DBVT1G-Q*	SC-74A	H1	Q4	3000 / Tape & Reel

†For complete information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.

PIN 1 ORIENTATION IN TAPE AND REEL



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SC-74A-5 3.00x1.50x0.95, 0.95P CASE 318BQ **ISSUE C** DATE 26 FEB 2024 NOTES: 5X b ⊕ 0.20 M C A B DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018. 2. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES). В 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, Ē 4 E1 PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. MILLIMETERS ○ 0.15 C DIM NOM. MIN. MAX. 2X е 0.90 1.00 1.10 А A A1 0.01 0.18 0.10 0.95 REF Α2 TOP VIEW 0.25 0.37 0.50 b DETAIL A (A2) 0.10 0.18 0.26 С Α D 2.85 3.00 3.15 Ε 2.75 BSC E1 1.35 1.50 1.65 0.05 C SEATING е 0.95 BSC Α1 Ċ PLANE END VIEW SIDE VIEW L 0.20 0.40 0.60 L1 0.62 REF 0.25 BSC 12 GAUGE PLANE L2 5° 10° Θ 0° 1.90 0.95 Ð, (L1)"A" DETAIL SCALE 2:1 2.40 GENERIC **MARKING DIAGRAM*** 1.00 0.70 XXX M= -O RECOMMENDED MOUNTING FOOTPRINT* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING XXX = Specific Device Code = Date Code Μ TECHNIQUES REFERENCE MANUAL, SOLDERRM/D. = Pb-Free Package (Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •" may or may not be present. Some products may not follow the Generic Marking. Electronic versions are uncontrolled except when accessed directly from the Document Repository. **DOCUMENT NUMBER:** 98AON66279G Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** SC-74A-5 3.00x1.50x0.95, 0.95P PAGE 1 OF 1

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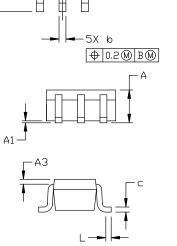
DATE 11 APR 2023



SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

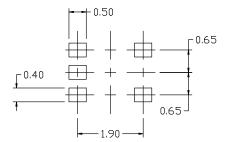
NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE. NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.



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F1



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS				
MIM	MIN.	NDM,	MAX.		
А	0.80	0.95	1.10		
A1			0.10		
AЗ		0.20 REF	-		
b	0.10	0.20	0.30		
С	0.10		0.25		
D	1.80	2.00	2.20		
E	2.00	2.10	2,20		
E1	1.15	1.25	1.35		
e		0.65 BS	С		
L	0.10	0.15	0.30		

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

M = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

DESCRIPTION:	SC-88A (SC-70-		ns are uncontrolled except w	vhen stamped "CONTROLLED (COPY" in red. PAGE 1 OF 1
DOCUMENT NUMBER:	98ASB42984B			t when accessed directly from	
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p	ype is not called refer to the device
STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	E

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